



Description

JMT P-channel Enhancement Mode Power MOSFET

Features

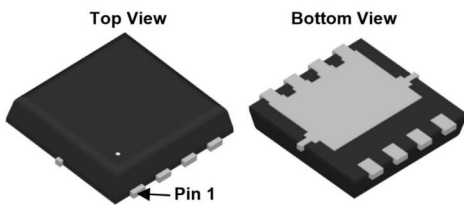
- $V_{DS} = -20V$, $I_D = -55A$
 $R_{DS(ON)} < 8.3m\Omega$ @ $V_{GS} = -4.5V$
 $R_{DS(ON)} < 10.4m\Omega$ @ $V_{GS} = -2.5V$
- High Power and Current Handling Capability
- Lead Free Product is Acquired
- Surface Mount Package

Application

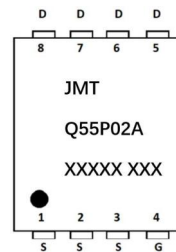
- PWM Applications
- Load Switch



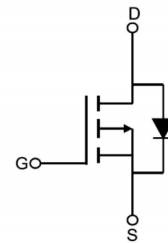
100% UIS TESTED!
100% ΔV_{ds} TESTED!



PDFN3x3-8L



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
JMTQ55P02A	JMTQ55P02A	TAPING	PDFN3x3-8L	13inch	5000	50000

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	-55
		$T_C = 100^\circ C$	-35
I_{DM}	Pulsed Drain Current ^{note1}	-220	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}	90	mJ
P_D	Power Dissipation $T_C = 25^\circ C$	66	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.9	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -20V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.65	-1.0	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} =-4.5V, I _D =-15A	-	6.6	8.3	mΩ
		V _{GS} =-2.5V, I _D =-12A	-	8	10.4	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f = 1.0MHz	-	4770	-	pF
C _{oss}	Output Capacitance		-	570	-	pF
C _{rss}	Reverse Transfer Capacitance		-	502	-	pF
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-15A, V _{GS} =-4.5V	-	56	-	nC
Q _{gs}	Gate-Source Charge		-	8	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	16	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =-10V, I _D =-13A, R _{GEN} =2.7Ω, V _{GS} =-10V	-	11	-	ns
t _r	Turn-on Rise Time		-	110	-	ns
t _{d(off)}	Turn-off Delay Time		-	157	-	ns
t _f	Turn-off Fall Time		-	160	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-55	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-220	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S =-30A	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	T _J =25°C, I _S =-15A,	-	23	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=-100A/μs	-	14	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25°C, V_{DD}=-10V, V_G=-10V, R_G=25Ω, L=0.5mH, I_{AS}=-19A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure 1: Output Characteristics

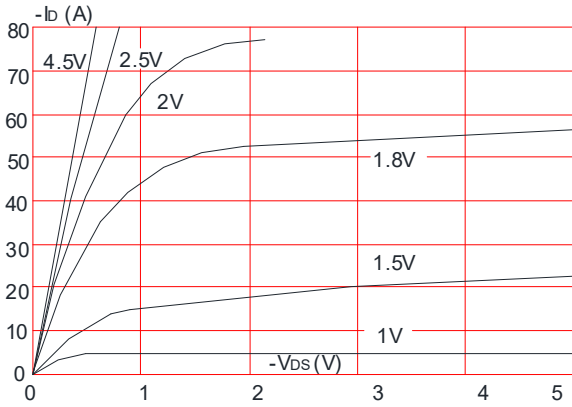


Figure 2: Typical Transfer Characteristics

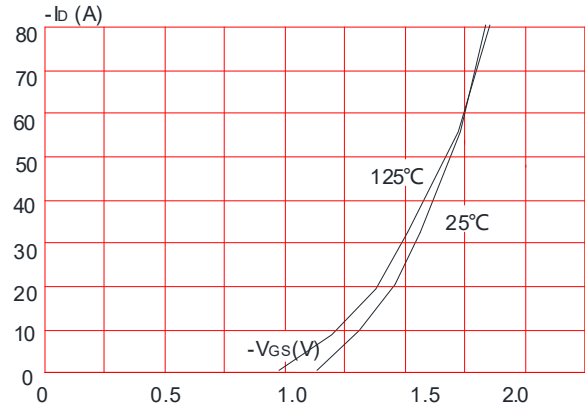


Figure 3: On-resistance vs. Drain Current

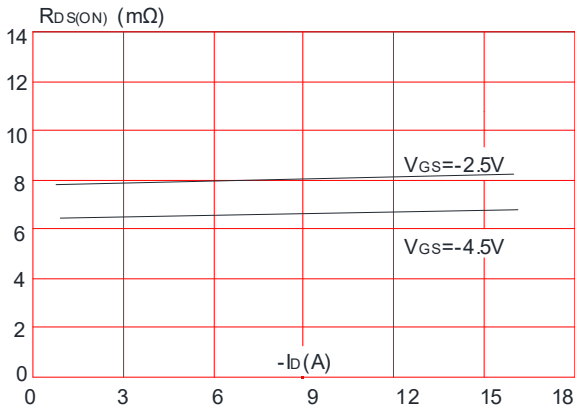


Figure 4: Body Diode Characteristics

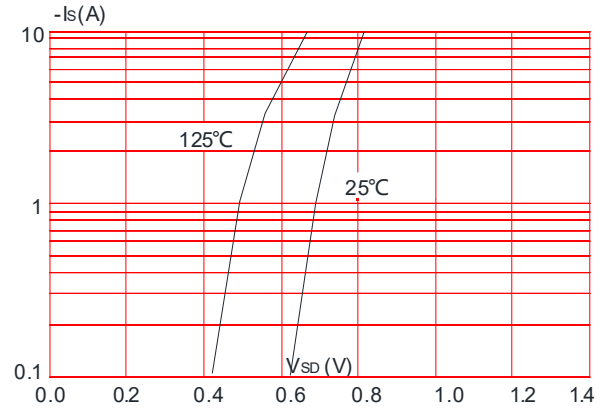


Figure 5: Gate Charge Characteristics

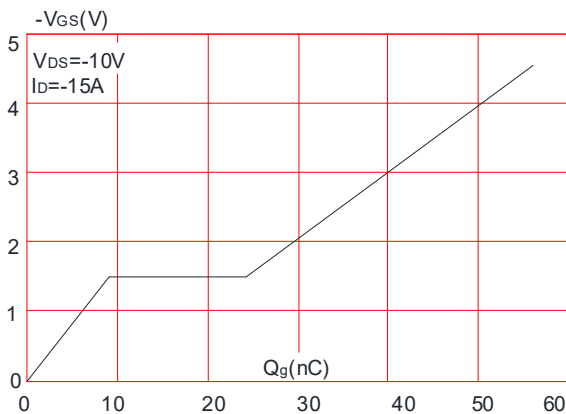


Figure 6: Capacitance Characteristics

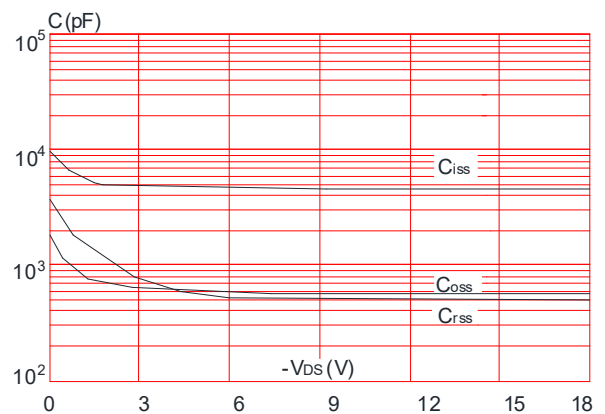




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

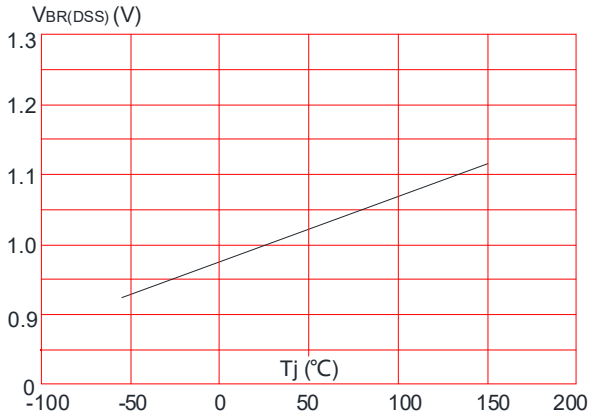


Figure 8: Normalized on Resistance vs. Junction Temperature

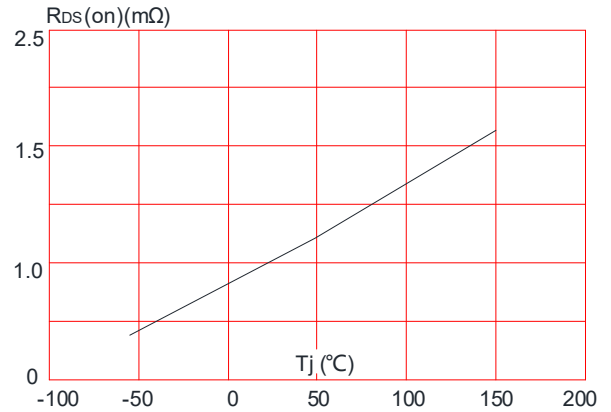


Figure 9: Maximum Safe Operating Area

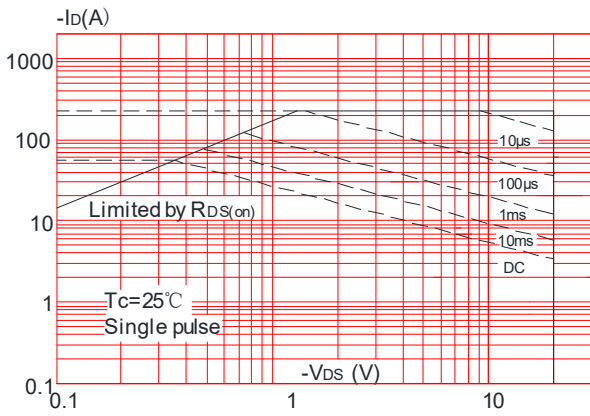


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

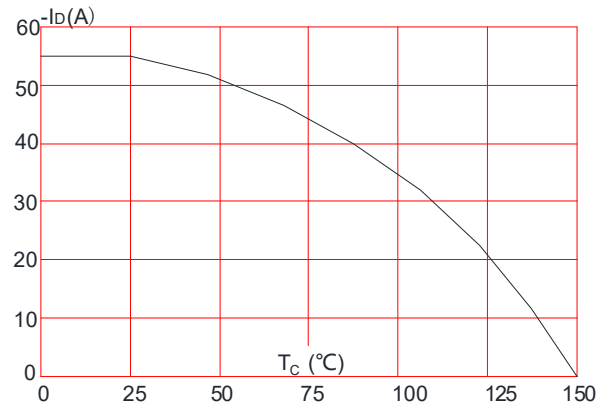
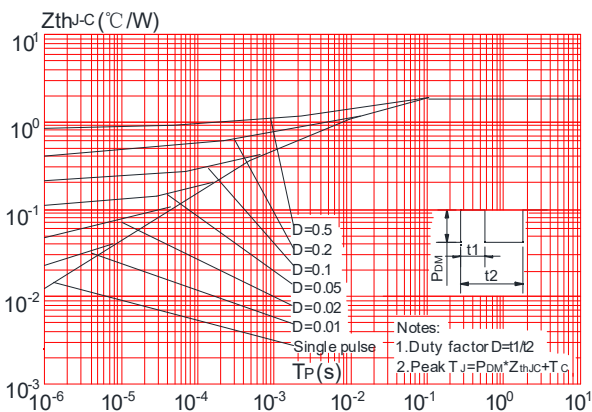
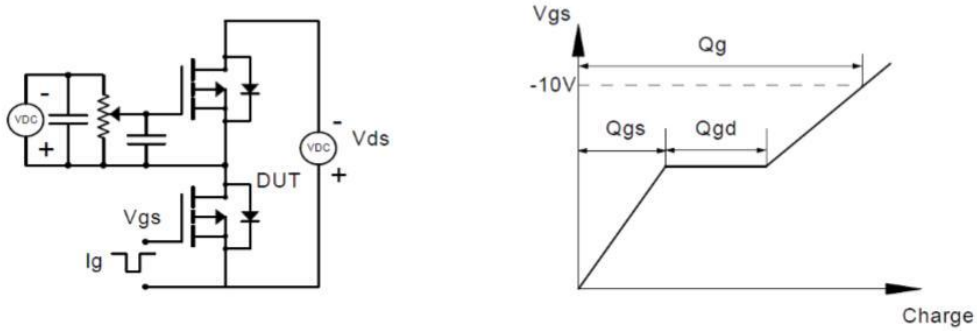


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

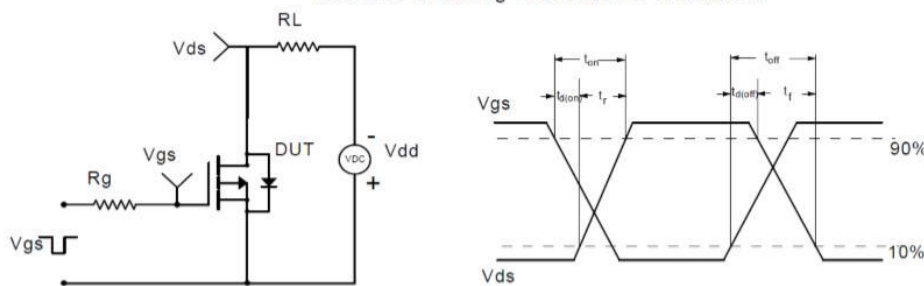


Test Circuit

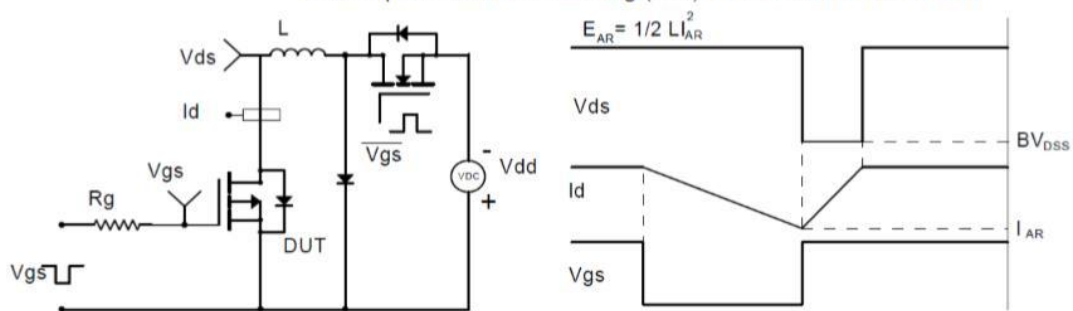
Gate Charge Test Circuit & Waveform



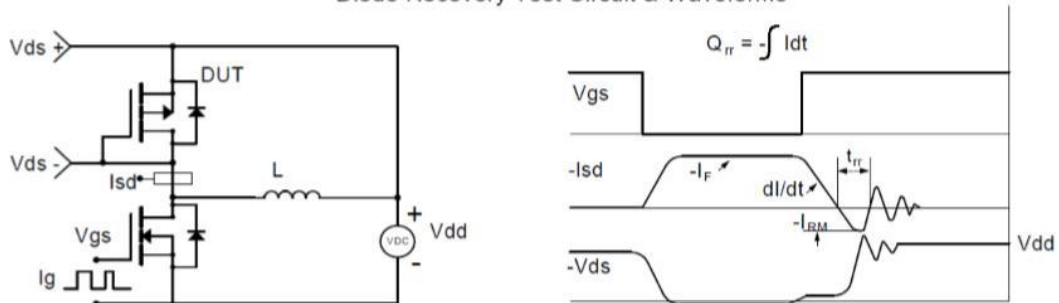
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

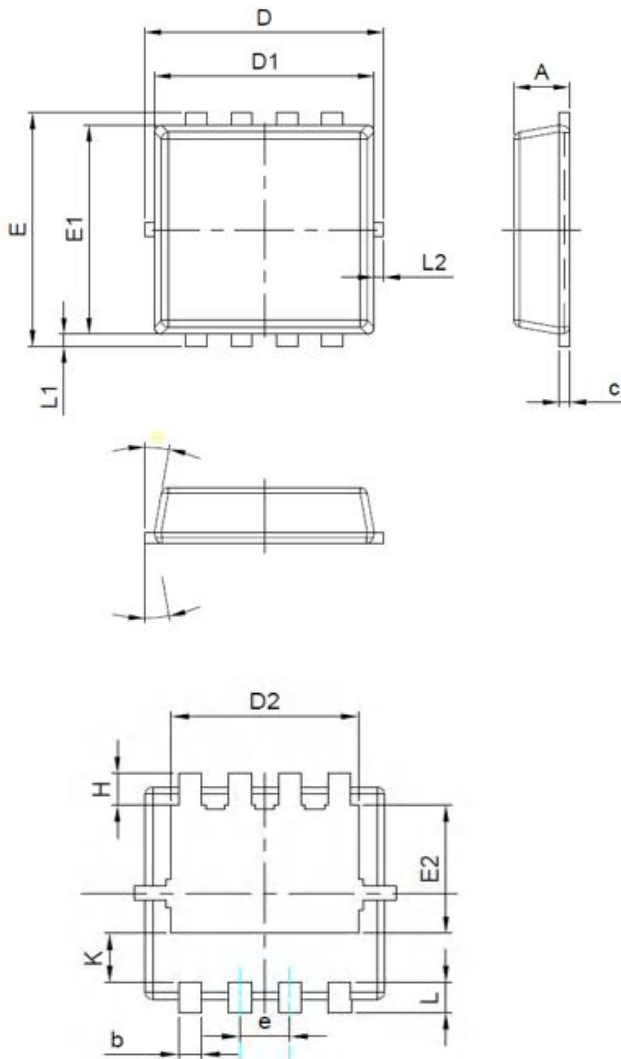


Diode Recovery Test Circuit & Waveforms





Package Mechanical Data-PDFN3x3-8L



COMMON DIMENSIONS
(UNITS OF MEASURE = MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.80	0.90
b	0.25	0.30	0.39
c	0.14	0.15	0.25
D	3.20	3.30	3.40
D1	3.00	3.15	3.30
D2	2.35	2.45	2.55
e	0.65 BSC		
E	3.25	3.35	3.45
E1	2.85	3.00	3.15
E2	1.635	1.735	1.835
H	0.33	0.48	0.63
K	0.585	0.685	0.785
L	0.30	0.40	0.50
L1	0.05	0.15	0.25
L2	-	-	0.15
⊙	8°	10°	12°

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